

IMP-4A/540D MOS/LSI 4-bit interface logic unit (FILU)

general description

The IMP-4A/540D 4-bit interface logic unit (FILU) is a member of a new family of microprocessor elements. It is a monolithic MOS/LSI circuit utilizing standard P-channel, enhancement mode, silicon gate technology. It is used with a CROM and RALU to provide the IMP-4 microprocessor with 16 flags, an 8 jump condition multiplexer, an address register, program counter and 6-level program counter stack. For ease of interfacing to memory and peripherals the FILU provides a 12-bit address bus and a 4-bit bidirectional data bus.

The IMP-4 system user is provided with two jump conditions: INT for interrupts and UJMPC for general purpose use. A flag output from the RALU is available as a general purpose flag.

The FILU operates on +5V and -12V supplies with 4-phase, non-overlapping clocks. Signals which are intended for interface with the RALU and CROM are MOS level.

The address bus and WRM, WRP, and RDP flags interfaces to TTL levels through LM365 sense amps and the data bus interfaces through DM8833 transceivers.

features

High speed

Standard supplies

+5V, −12V

■ Bipolar compatibility

Drives TTL 40 pin DIP

Standard package

500 kHz

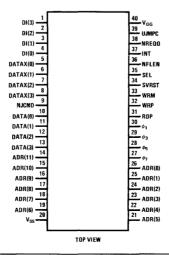
 3-package microprogrammable processor (1 CROM, 1 RALU, and 1 FILU)

applications

- General purpose processor
- Process controllers
- Machine tool controllers
- Small business machines
- Terminal controllers
- Test system and instrument control
- Traffic controller
- Electronic cash register
- Peripheral controllers
- Data acquisition systems

connection diagram

Dual-In-Line Package



absolute maximum ratings (Note 1)

All Input or Output Voltages with Respect

to Most Positive Supply Voltage V_{SS}

Operating Temperature Range Storage Temperature Range

Power Dissipation
Lead Temperature (Soldering, 10 seconds)

+0.3V to -20V 0°C to +70°C

-65°C to +150°C

1.3W Maximum at +25°C

300°C

electrical characteristics T_A = 25°C, V_{GG} = -12V ±5%, V_{SS} = +5V ±5%

PARAMETER	CONDITIONS	MIN (Note 3)	ТҮР	MAX (Note 3)	UNITS
Logic "1" Input (MOS and TTL) (V _{IN (1)}) (Note 2)		V _{SS} -1.0			V
Logic "0" Input (MOS) (V _{IN (0)}) (Note 4)				V _{SS} -7.0	٧
Logic "0" Input (TTL) (V _{IN(0)})				V _{SS} -4.2	٧
Logic "0" Input Current (TTL) (I _{IN (0)})	V _{IN} = 0V			-1.6	mA
Input Leakage Current (MOS) (IL)	V _{IN} = +5V to -12V			2.0	μΑ
Logic "1" Output (MOS) (V _{OUT (1)})		V_{SS}			V
Logic "0" Output (MOS) (V _{OUT(0)})				V _{SS} -5.0	V
Logic "1" Output (TTL – DM8833) (V _{OUT(1)})		2.4			V
Logic "0" Output (TTL $-$ DM8833) ($V_{OUT(0)}$)	I _{OUT} = 100μA			0.4	V
Pull-up Transistor "on" Resistance (R _{PULL-UP}) (Note 2)	V _{IN} = V _{SS} - 1.0V	3.5		5.5	kΩ
Signal Line Input Capacitance (C _S) (See Figure 4A) DATA (0 - 3) DATAX (0 - 3) NFLEN DI (0 - 3) NREQ0 INT UJMPC	V _{IN} = V _{SS} , f _T = 500 kHz			10 15 20 10 15 10	pF pF pF pF pF pF
Clock Input Capacitance (C_C) (See Figure 4A), Clocks ϕ_1 , ϕ_3 , ϕ_5 , ϕ_7	$V_{IN} = V_{SS}$, $f_T = 500 \text{ kHz}$			70	pF
Clock "1" Level (V _{ϕ(1)})		V _{SS} -1.0		V_{SS}	٧
Clock "0" Level (V _{\phi(0)})		V_{GG}		V _{GG} +1.0	V
LOAD Capacitance for DI $(0-3)$, DATAX $(0-3)$, DATA $(0-3)$				25	pF
Leakage Current ADR, WRM, WRP, and RDP Output "0"				10	μΑ
Load Current ADR, WRM, WRP, and RDP Output "1"		0.800			mA
Power Dissipation (P _D)	f = 500 kHz		750		mW

Note 1: Maximum ratings indicate limits beyond which permanent damage may occur. Continuous operation at these limits is not intended and should be limited to those conditions specified under dc electrical characteristics.

Note 2: Internal pull-up provided for TTL inputs. Refer to Figure 3 and text,

Note 3: Max = most positive; Min = most negative.

Note 4: $V_{SS} - 5.5$ for DI(0) - (3).

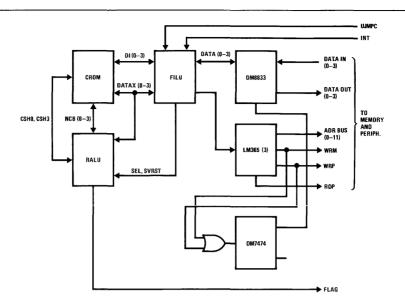


FIGURE 1. Systems Block Diagram

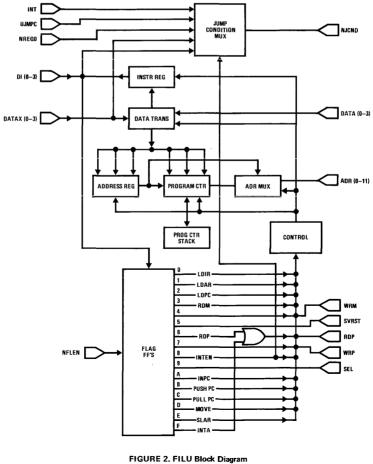
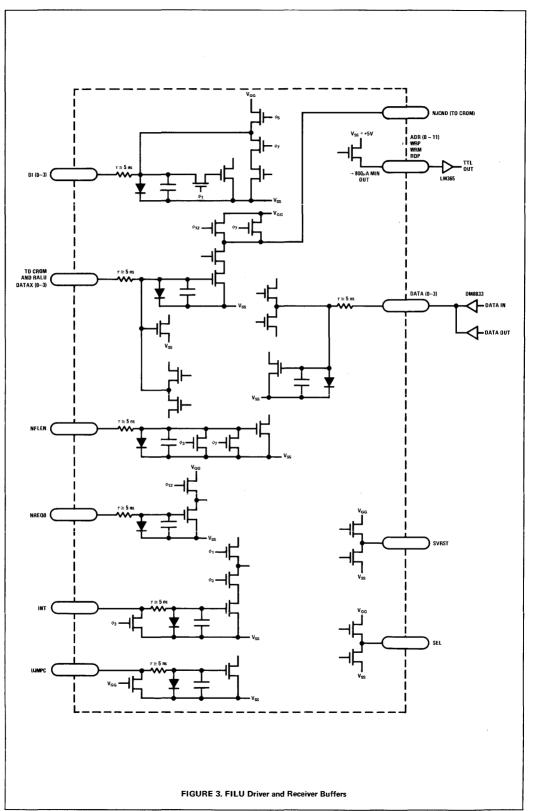
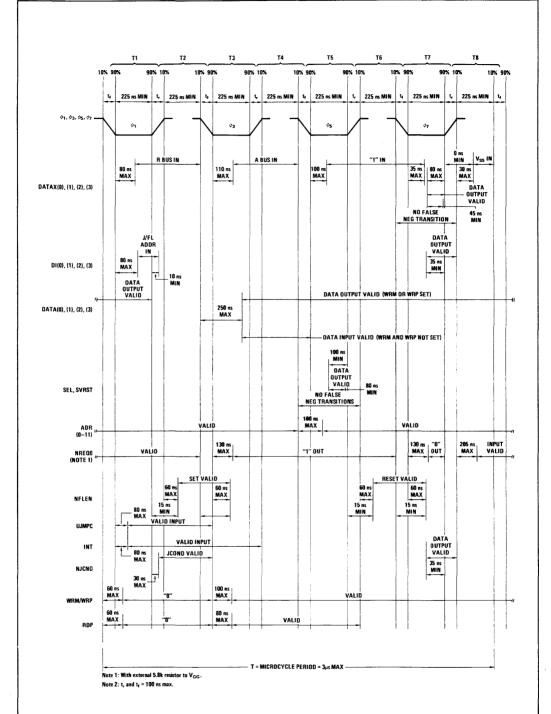


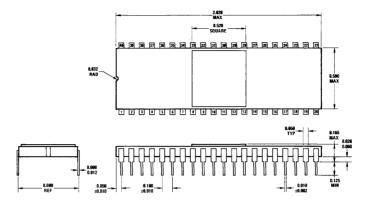
FIGURE 2. FILO Block Diagram





FILU Signal Timing Specifications ($T_A = 25^{\circ}C$, $V_{SS} = +5V \pm 5\%$, $V_{GG} = -12V \pm 5\%$)

physical dimensions



Cavity Dual-In-Line Package (D)
Order Number IMP-4A/540D

Manufactured under one or more of the following U.S. patents: 3083062, 3189758, 3231797, 3303356, 3317671, 3323071, 3381071, 3408542, 3421025, 3426423, 3440498, 3518750, 3519897, 3557431, 3560765, 3566218, 3571630, 3575609, 35993069, 3597640, 3607469, 3617859, 3631312, 3633052, 3638131, 3648071, 3551565, 3633248.

National Semiconductor Corporation
2900 Semiconductor Drive, Santa Clara, California 95051, (408) 732-5000/TWX (910) 339-9240
National Semiconductor GmbH
808 Fuerstenfeldbruck, Industriestrasse 10, West Germany, Tele. (08141) 1371/Telex 05-27649
National Semiconductor (UK) Ltd.
Larkfield Industrial Estate, Greenock, Scotland, Tele. (0475) 33251/Telex 778-632

